IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Sheu, et al.	Docket No.:	TSM03-0140
Serial No.:	10/619,828	Art Unit:	2811
Filed:	July 15, 2003	Examiner:	TBD
For:	Self-Aligned MOSFET having an Oxide Region below the Channel		

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Date of Deposit: March 25, 2004

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IDS Forms PTO/SB/08a and 08b (3 pages) citing (41) references
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Respectfully submitted,

Natalie Swider

Natalie Swider
Legal Assistant

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
Tel: 972-732-1001
Fax: 972-732-9218

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Commissioner for Patents
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Dear Sir:

Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed forms PTO/SB/08a & 08b that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

Respectfully submitted,

25 MAR 2004
Date

Steven H. Slater
Attorney for Applicants
Reg. No. 35,361

Slater & Matsil, L.L.P.
17950 Preston Rd., Suite 1000
Dallas, TX 75252
(972) 732-1001 (phone)
(972) 732-9218 (fax)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

Complete if Known	
Application Number	10/619,828
Filing Date	07/15/2003
First Named Inventor	Sheu, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM03-0140

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number: Number - Kind Code[2] (*if known*)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US-4,631,803	12-30-1986	Hunter, *et al.*	
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Examiner Initials*	Cite No.[1]	Foreign Patent Document: Country Code[3] - Number[4] - Kind Code[5] (*if known*)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	2	of	3

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Application Number	10/619,828
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First Named Inventor	Sheu, et al.
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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	31	MATTHEWS, J.W., *et al.*, "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
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